Unit in mm

TOSHIBA ALLOY-FREE LIGHT TRIGGER THYRISTOR

SL1500GX23

HIGH POWER CONTROL APPLICATIONS

Repetitive Peak Off-State Voltage : V_{DRM} = 4000V

Repetitive Peak Reverse Voltage : VRRM

 $: I_{T(AV)} = 1500A$ Average On-State Current

Light Trigger Power : PLT: 10mW (Max.)

Turn-Off Time : $t_0 = 400 \mu s$ (Max.)

Critical Rate of Rise of On-State Current

: $di/dt = 250A/\mu s$

Critical Rate of Rise of Off-State Voltage

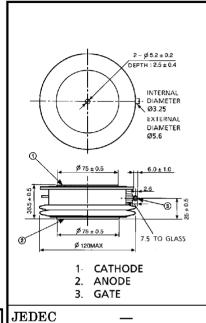
: $dv/dt = 1500V/\mu s$

Flat Package

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	V _{DRM} V _{RRM}	4000	V	
Non-Repetitive Peak Reverse Voltage (Non-Repetitive ≤ 5 ms, $T_j = 0 \sim 125$ °C)	$v_{ m RSM}$	4400	V	
R.M.S On-State Current	IT (RMS)	2355	Α	
Average On-State Current	I _{T (AV)}	1500	Α	
Peak One Cycle Surge On-State Current (Non-Repetitive)	I_{TSM}	30000 (50Hz) 33000 (60Hz)	A	
I ² t Limit Value	${f I}^2{f t}$	4500×10^{3}	A^2s	
Critical Rate of Rise of On-State Current (Note)	di/dt	250	A/μs	
Junction Temperature	T_{j}	-40~125	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$\mathrm{T_{stg}}$	-40~125	$^{\circ}\mathrm{C}$	
Mounting Force	_	39.2±3.9	kN	

Note: $V_D=1/2$ Rated, $T_i=120$ °C



JEDEC	_
EIAJ	_
TOSHIBA	13-120L1A

Weight: 1700g

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ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION		MAX.	UNIT
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current	I _{DRM} I _{RRM}	$V_{ m DRM} = V_{ m RRM} = { m Rated}$ $T_{ m j} = 125 { m ^{\circ}C}$		120	mA
Peak On-State Voltage	$ m V_{TM}$	$I_{TM} = 5000A, T_j = 25^{\circ}C$		2.3	V
Light Trigger Power	$P_{ m LT}$	$T_{j} = -40^{\circ}$:	_	mW
		$V_D=12V, R_L=6\Omega$ $T_j=25^{\circ}C$		10	
Delay Time	$^{ m t_d}$	$V_D=1/2$ Rated, $T_j=25$ °C		4	μs
Gate Turn-On Time	t_{gt}	P_{L} =20mW		6	μs
Turn-Off Time	t_{q}	$egin{array}{l} I_{T}\!=\!1200 A, \ V_{R}\!\!\geq\!200 V \ dv \ / \ dt\!=\!25 V \ / \ \mu s, \ T_{j}\!=\!115^{\circ}C \ V_{DRM}\!=\!1 \ / \ 2 \ Rated \end{array}$		400	μs
Holding Current	${ m I_H}$	$T_j=25$ °C, $R_L=6\Omega$		300	mA
Critical Rate of Rise of	dv / dt	V _{DRM} =1/2 Rated, T _j =125°C	1500		V/μs
Off-State Voltage	uv/ut	Gate Open, Exponential Rise	1500		vγμs
Thermal Resistance (Junction to Case)	$ m R_{th~(j-f)}$	DC		0.02	°C/W

